

TABLES FOR SYNTHESIS OF THE TWO-LINKS ENTRANCE MATCHING CIRCUIT OF THE POWERFUL HIGH-FREQUENCY TRANSISTOR WITH ACCOUNT OF POWER LOSSES CAUSED BY MUTUAL INDUCTION

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The techniques of synthesis of broadband entrance matching LC-circuits of the powerful high-frequency transistors are considered. These techniques are taking into account the differences of values of equivalent inductances of entrance circuits of transistor cells separately caused by inter-induction. It is shown, that this factor may be used for reduction of losses of input power by synthesis of the transistor matching circuit with an edge kind of frequency dependences of power transmitting factor, realized due to regular distribution of resonance peaks of the internal LC-link of the separate cells in the matching band.